

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

#8
Pre Amt A
RABEP
9/25/01

In re Application of

Atty. Docket

MARCEL E.I. BROEKAART ET AL

NL 000314

Serial No.

Filed: CONCURRENTLY

A METHOD OF MANUFACTURING A SEMICONDUCTOR DEVICE

Honorable Commissioner of Patents and Trademarks
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to calculation of the filing fee and examination, please
amend the above-identified application as follows:

IN THE CLAIMS

Please amend the claims as follows:

5. (Amended) A method as claimed in claim 2, characterized in that the etch stop layer is applied to the top surface portion and the sidewall portions of the conductor as well as to portions of the semiconductor substrate which are not covered by the conductor.

6. (Amended) A method as claimed in claim 1, characterized in that the conductor is provided while comprised at least in part of a material selected from a group comprising aluminum, copper and tungsten.